# PDTA143EMB



PNP resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$ Rev. 1 — 14 May 2012 Product data sh

**Product data sheet** 

#### 1. **Product profile**

### 1.1 General description

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC143EMB.

#### 1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs
- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm

### 1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Replaces general-purpose transistors in digital applications
- Mobile applications

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mΑ
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)	1	<sub>3</sub>
3	0	output (collector)	2 3	1 R1
			Transparent top view	∏R2 ∏
			SOT883B (DFN1006B-3)	sym003

# 3. Ordering information

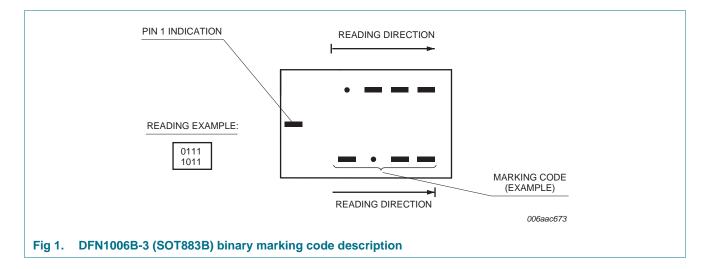
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PDTA143EMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PDTA143EMB	0010 0111



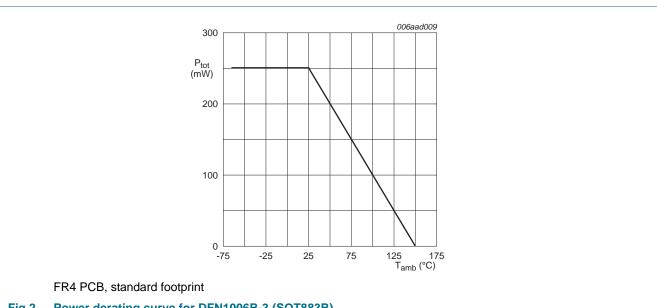
# **Limiting values**

Table 5. **Limiting values** 

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-50	V
$V_{CEO}$	collector-emitter voltage	open base		-	-50	V
$V_{EBO}$	emitter-base voltage	open collector		-	-10	V
VI	input voltage	positive		-	10	V
		negative		-	-30	V
Io	output current			-	-100	mA
I <sub>CM</sub>	peak collector current	pulsed; t <sub>p</sub> ≤ 1 ms		-	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
$T_{stg}$	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



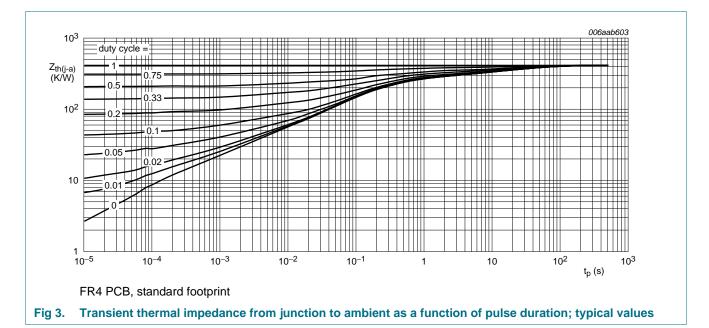
Power derating curve for DFN1006B-3 (SOT883B)

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

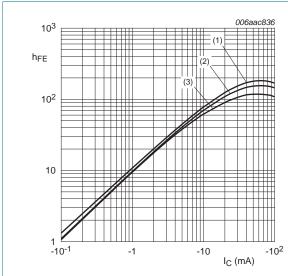


### 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	-1	μΑ
	current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}; T_j = 150 \text{ °C}$		-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	-900	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; $T_{amb}$ = 25 °C		30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -10 mA; $I_B$ = -0.5 mA; $T_{amb}$ = 25 °C		-	-	-150	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE}$ = -5 V; $I_{C}$ = -100 $\mu$ A; $T_{amb}$ = 25 °C		-	-1.1	-0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE}$ = -0.3 V; $I_{C}$ = -20 mA; $T_{amb}$ = 25 °C		-2.5	-1.9	-	V
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	
C <sub>C</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 \text{ °C}$		-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	<u>[1]</u>	-	180	-	MHz

#### [1] Characteristics of built-in transistor.



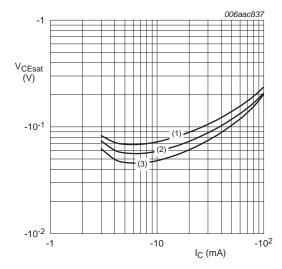
 $V_{CE} = -5 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 4. DC current gain as a function of collector current; typical values



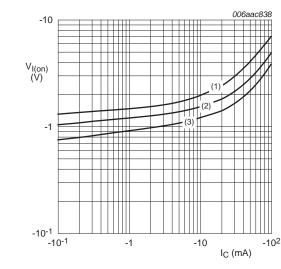
 $I_{\rm C}/I_{\rm B} = 20$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



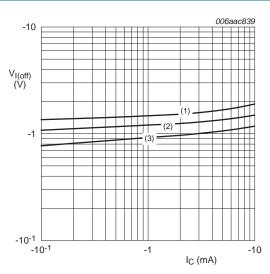
$$V_{CE} = -0.3 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 6. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 V$$

(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 7. Off-state input voltage as a function of collector current; typical values

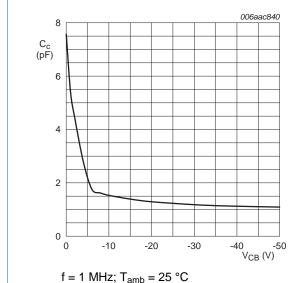
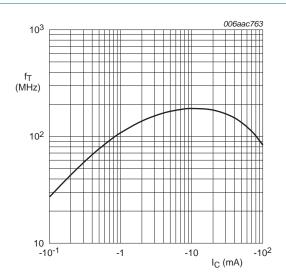


Fig 8. Collector capacitance as a function of collector-base voltage; typical values



 $V_{CE} = -5 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$ 

Fig 9. Transition frequency as a function of collector current; typical values of built-in transistor

### 8. Test information

### 8.1 Quality information

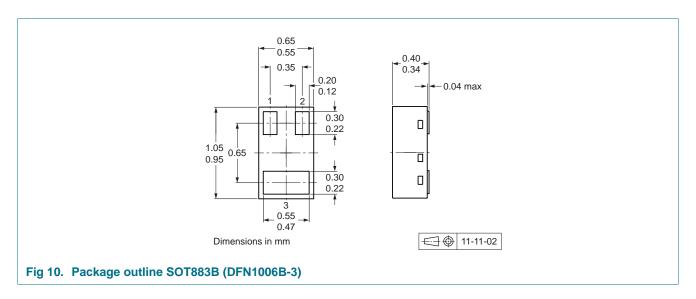
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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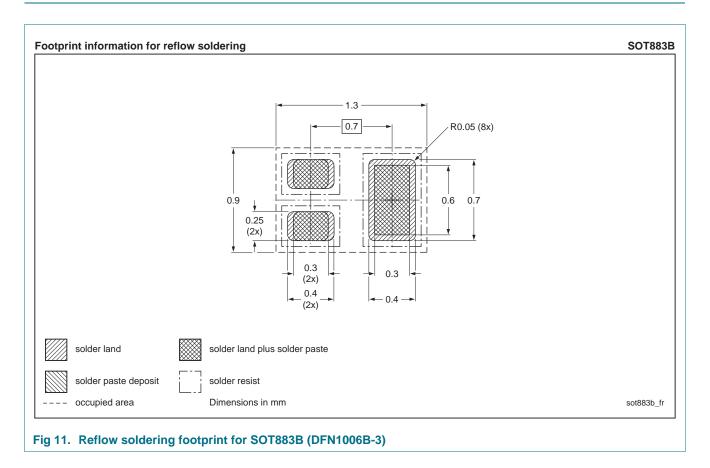
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# 9. Package outline



# 10. Soldering





# 11. Revision history

### Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA143EMB v.1	20120514	Product data sheet	-	-

## 12. Legal information

#### 12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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